

Title (en)

A METHOD OF TREATING A SEMI-CONDUCTOR WAFER

Title (de)

BEHANDLUNGSVERFAHREN FÜR EINE HALBLEITENDE SCHEIBE

Title (fr)

PROCEDE DE TRAITEMENT POUR GALETES SEMI-CONDUCTRICES

Publication

EP 0708982 A1 19960501 (EN)

Application

EP 95918082 A 19950510

Priority

- GB 9501057 W 19950510
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Abstract (en)

[origin: WO9531823A1] A method of treating a semi-conductor wafer is described in which a short-chain polymer is deposited on the wafer to planarise surface features on the wafer and a diffusion layer is deposited on the surface of the polymer layer to allow moisture to be released from the polymer at a controlled rate.

IPC 1-7

H01L 21/312; **H01L 21/316**

IPC 8 full level

H01L 21/312 (2006.01); **H01L 21/316** (2006.01)

CPC (source: EP KR)

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Citation (search report)

See references of WO 9531823A1

Designated contracting state (EPC)

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GB 9501057 W 19950510; CA 2167085 A 19950510; CN 95190426 A 19950510; EP 95918082 A 19950510; GB 9409713 A 19940514; JP 52943695 A 19950510; KR 19960700128 A 19960111; TW 84106199 A 19950616